

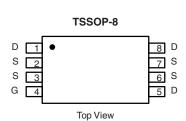
# P-Channel 20-V (G-S) MOSFET

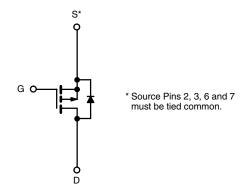
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
	$0.012$ at $V_{GS} = -4.5 \text{ V}$	- 9.0		
-20	0.015 at V <sub>GS</sub> = - 2.5 V	- 7.8		
	0.020 at V <sub>GS</sub> = - 1.8 V	- 6.0		

#### **FEATURES**

- Halogen-free
- TrenchFET® Power MOSFETs







P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	-20		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		
Continuous Drain Current /T 150 °C\8	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 9.0	-7.8	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 6.8	-5.8	
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	- 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.35	- 0.95	
Mariana Barra Birainatian	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.5	1.05	- w
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.0	0.67	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipania Ingation to Applicati	t ≤ 10 s	- R <sub>thJA</sub>	65	83	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	43	52	

Notes: a. Surface Mounted on 1" x 1" FR4 board.

E-mail: China@VBsemi TEL:86-755-83251052

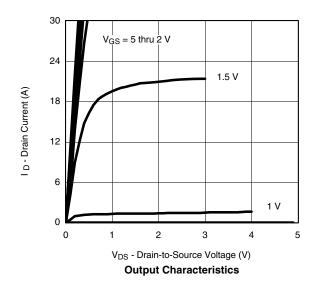


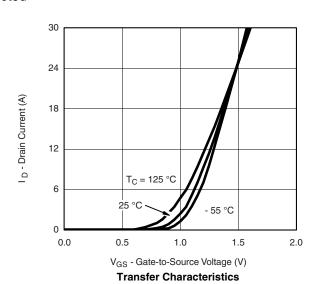
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -450 \mu A$	- 0.45	-	1.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	_	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μA	
	I <sub>DSS</sub>	$V_{DS}$ = -20V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C			- 25		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS}$ - 5 V, $V_{GS}$ = - 4.5 V	- 20			Α	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS}$ - 4.5 V, $I_D$ = - 8.0 A		0.010			
	R <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -7.0 \text{ A}$		0.012		Ω	
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 5.8 A		0.016			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -5 \text{ V}, I_{D} = -8.0 \text{ A}$		44		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 1.5 A, V <sub>GS</sub> = 0 V		- 0.56	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			46	70		
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ = - 10 V, $V_{GS}$ = - 4.5 V, $I_D$ = - 8.0 A		5		nC	
Gate-Drain Charge	$Q_{gd}$			15.5		1	
Turn-On Delay Time	t <sub>d(on)</sub>			45	70		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R$ = 6 $\Omega$		85	130		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		220	400	ns	
Fall Time	t <sub>f</sub>			155	235		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.5 A, di/dt = 100 A/μs		140	210		

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

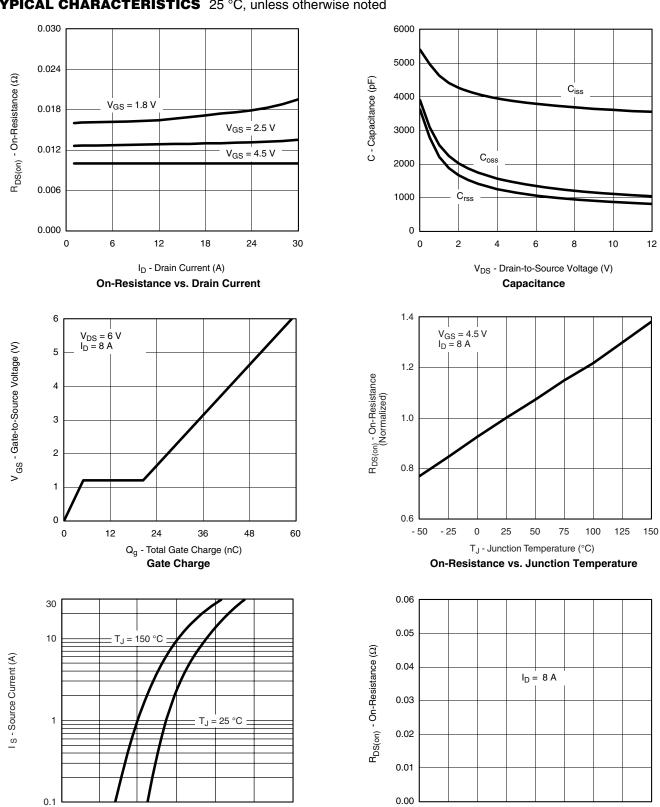
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



0

2

3

4

On-Resistance vs. Gate-to-Source Voltage

V<sub>GS</sub> - Gate-to-Source Voltage (V)

5

6

7

0.0

0.2

0.4

0.6

V<sub>SD</sub> - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage

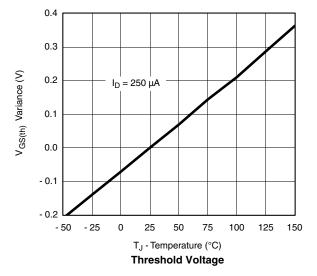
0.8

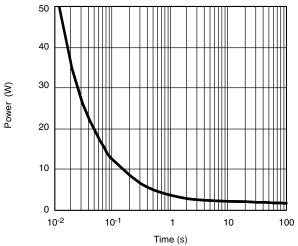
1.0

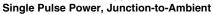
1.2

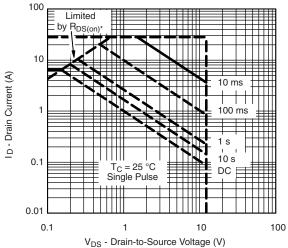


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



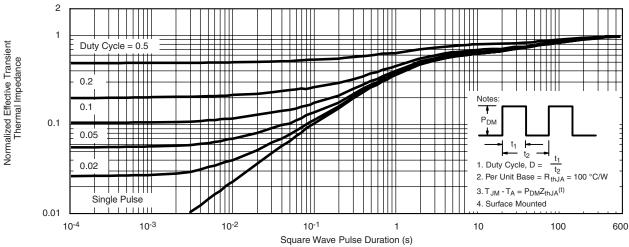






 $^{\star}$   $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

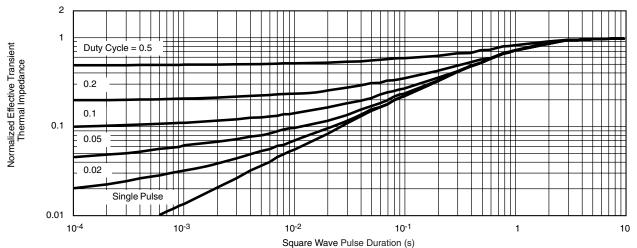
#### Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

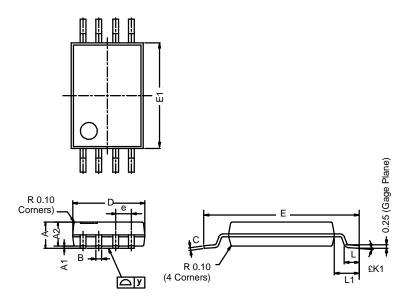


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP: 8-LEAD

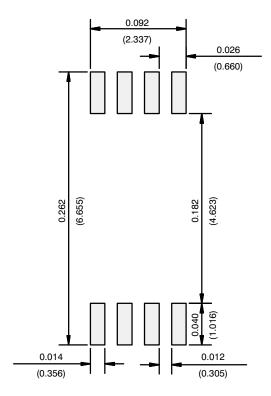
**JEDEC Part Number: MO-153** 



	MILLIMETERS				
Dim	Min	Max			
Α	-	-	1.20		
A <sub>1</sub>	0.05	0.10	0.15		
A <sub>2</sub>	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
Е	6.20	6.40	6.60		
E <sub>1</sub>	4.30	4.40	4.50		
е	-	0.65	_		
L	0.45	0.60	0.75		
L <sub>1</sub>	0.90	1.00	1.10		
Υ	-	-	0.10		
£K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



#### **RECOMMENDED MINIMUM PADS FOR TSSOP-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

E-mail: China@VBsemi TEL:86-755-83251052



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